

What is claimed is:

1. A method for improving reliability of an etching apparatus and a deposition apparatus, the method comprising the steps of:

preparing a reaction unit using chlorine series gas; and

generating a plasma including at least one of hydrogen and nitrogen in the reaction unit to remove a residual remaining in a reaction tube of the reaction unit.

2. The method as claimed in claim 1, wherein the plasma including hydrogen comprises argon of 5 to 90%.

3. The method as claimed in claim 1, wherein the plasma including nitrogen comprises hydrogen of 5 to 50%.

4. The method as claimed in claim 1, wherein the plasma including nitrogen comprises argon of 5 to 90%.

5. The method as claimed in claim 1, wherein the plasma including nitrogen comprises hydrogen of 5 to 50% and argon of 5 to 90%.

6. A method for improving reliability of an etching apparatus and a deposition apparatus, the method comprising the steps of:

preparing at least one of an etching apparatus and a deposition apparatus, each of the apparatuses using a chlorine series gas; and

generating a plasma including at least one of hydrogen and nitrogen in one of the etching apparatus and the deposition apparatus to remove a residual remaining in a reaction tube of the apparatus.

7. The method as claimed in claim 6, wherein the plasma including hydrogen comprises argon of 5 to 90%.

8. The method as claimed in claim 6, wherein the plasma including nitrogen comprises hydrogen of 5 to 50%.

9. The method as claimed in claim 6, wherein the plasma including nitrogen comprises argon of 5 to 90%.

10. The method as claimed in claim 6, wherein the plasma including nitrogen comprises hydrogen of 5 to 50% and argon of 5 to 90%.